HAT2053M

Silicon N Channel Power MOS FET Power Switching

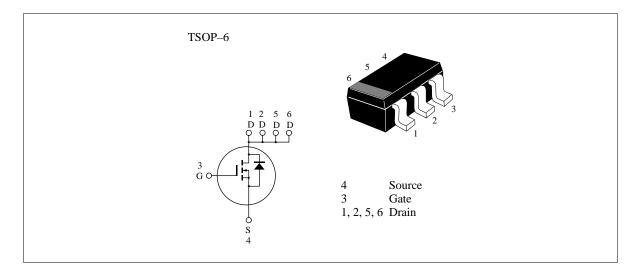
HITACHI

ADE-208-755C (Z) Preliminary 4th. Edition Mar. 2001

Features

- Low on-resistance
- Low drive current
- High density mounting
- 2.5V gate drive device can be driven from 3V source

Outline





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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	20	V
Gate to source voltage	V _{GSS}	±12	V
Drain current	I _D *2	6.1	A
Drain peak current	l _{D(pulse)} *1	24.4	A
Body-drain diode reverse drain current	*2 DR	6.1	A
Channel dissipation	Pch _(pulse) *2	2.0	W
	Pch _(continuous) *3	1.05	W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1 %

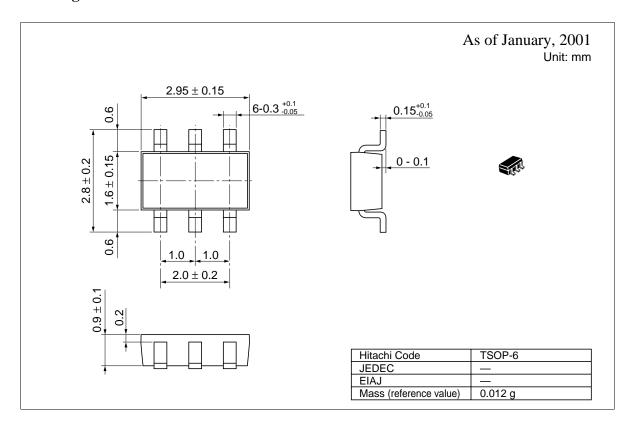
- 2. When using the alumina ceramic board (50 x 50 x 0.7 mm), PW 5s,Ta=25°C
- 3. When using the alumina ceramic board (50 x 50 x 0.7 mm) ,Ta=25°C

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	20	_	_	V	$I_{D} = 10 \text{mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 12V, V_{DS} = 0$
Zero gate voltege drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 20 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.4	_	1.4	V	$V_{DS} = 10V$, $I_D = 1mA$
Static drain to source on state	R _{DS(on)}		28	33	mΩ	$I_D = 3A, V_{GS} = 4.5V^{*1}$
resistance	$R_{\rm DS(on)}$	_	37	48	$m\Omega$	$I_D = 3A, V_{GS} = 2.5V^{*1}$
Forward transfer admittance	y _{fs}	6.0	10	_	S	$I_D = 3A, V_{DS} = 10V^{*1}$
Input capacitance	Ciss	_	570	_	pF	V _{DS} = 10V
Output capacitance	Coss	_	220	_	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss		160	_	pF	f = 1MHz
Turn-on delay time	t _{d(on)}	_	15	_	ns	$V_{GS} = 4.5V, I_{D} = 3A$
Rise time	t _r	_	100	_	ns	$R_L = 3.3\Omega$
Turn-off delay time	t _{d(off)}		90	_	ns	
Fall time	t _f	_	105	_	ns	
Body-drain diode forward voltage	V_{DF}	_	0.95	_	V	IF = 6.1A, $V_{GS} = 0^{*1}$
Body-drain diode reverse recovery time	t _{rr}	_	(50)	_	ns	$IF = 6.1A, V_{GS} = 0$ diF/ dt =20A/ μ s

Note: 1. Pulse test

Package Dimensions



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